15. MISCELLANOUS TRANSISTORS

IN ORDER OF: (1)CATEGORY,(2)TYPE NO.

LINE No.	2 TYPE No.	1 CATEGORY USE	STRUCTURE	MAT	DWG # Y200 s/a TO200 Ser.	CASE	DESCRIPTION
1#	40809	6	P-N	Ge	TO1	A	Matched Pair of AC127 and AC128.
2	AD810*	6	N	Si	TO71	PA	Pt 500mW(both sides);VBE(1-2)3.0mVmax;ΔVBE(1-2)/ΔT 15uV/°C
3	AD811*	6	N	Si	TO71	PA	Pt 500mW(both sides);VBE(1-2)1.5mVmax;ΔVBE(1-2)/ΔT 7.5uV/°C
4	AD812*	6	N	Si	TO71	PA	Pt 500mW(both sides);VBE(1-2)1.0mVmax;ΔVBE(1-2)/ΔT 5.0uV/°C
5	AD813*	6	N	Si	TO71	PA	Pt 500mW(both sides);VBE(1-2)0.5mVmax;ΔVBE(1-2)/ΔT 2.5uV/°C
6	AD814*	6	N	Si	TO71	PA	Pt 750mW(both sides);VBE(1-2)1.0mVmax;ΔVBE(1-2)/ΔT 5.0uV/°C
7	AD815*	6	N	Si	TO71	PA	Pt 750mW(both sides);VBE(1-2)1.0mVmax;ΔVBE(1-2)/ΔT 5.0uV/°C
8	AD816*	6	N	Si	TO71	PA	Pt 750mW(both sides);VBE(1-2)1.0mVmax;ΔVBE(1-2)/ΔT 5.0uV/°C
9	AD818	6	N	Si	TO52		hFE 150-600,VBE(1-2)1.0mVmax;ΔVBE(1-2)/ΔT 5uV/°C;BVCEO 20V
10	AD820	6	P	Si	TO71	PA	BVCBO 25V min;hFE100 min,Ic10uA,VCE5V;VBE(1-2)5.0mV max;ΔVBE(1-2)ΔT20uV/°C
11	AD821	6	P	Si	TO71	PA	ft 200MHz min;BVCBO 45Vmin;hFE 150-600,Ic 10uA,VBE(1-2)1.0mVmax;ΔVBE(1-2)/ΔT 5uV/°C
12	AD822	6	P	Si	TO71	PA	ft 200MHz min;BVCBO 60Vmin;hFE 200-600,Ic 10uA,VBE(1-2)0.5mVmax;ΔVBE(1-2)/ΔT 2.5uV/°C
13	AD830*	6	N	Si	TO78	PJ	Pt 750mW(both sides);VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 5.0uV/°Cmax;yfs 1/2 .99
14	AD831*	6	N	Si	TO78	PJ	Pt 750mW(both sides);VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 10uV/°Cmax;yfs 1/2 .99
15	AD832*	6	N	Si	TO78	PJ	Pt 750mW(both sides);VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 20uV/°Cmax;yfs 1/2 .99
16	AD833*	6	N	Si	TO78	PJ	Pt 750mW(both sides);VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 40uV/°Cmax;yfs 1/2 .99
17	AD833A*	6	N	Si	TO78	PJ	Pt 750mW(both sides);VGS(1-2)25mVmax;ΔVGS(1-2)/ΔT 75uV/°Cmax;yfs 1/2 .99
18	AD840*	6	N	Si	TO71	PJ	Pt 400mW(both sides);VGS(1-2)5.0mVmax;ΔVGS(1-2)/ΔT 5.0uV°Cmax;yfs(1-2)/yfs .6%
19	AD841*	6	N	Si	TO71	PJ	Pt 400mW(both sides);VGS(1-2)5.0mVmax;ΔVGS(1-2)/ΔT 10uV°Cmax;yfs(1-2)/yfs .6%
20#	ADY27*	6	P-A	Ge	F9d	CØ	hFE1/hFE2 1.25 max;Pt 27.5W;ICEV 150uA;ft 450kHz.
21	B1181MP	6	PNP	G	TO3	A	Matched Pairs within 5% 4.0V at 5.0 amps
22#	BC140-6*	6	N-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
23#	BC140-10*	6	N-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
24#	BC140-16*	6	N-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
25#	BC141-6*	6	N-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
26#	BC141-10*	6	N-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
27#	BC141-16*	6	N-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
28#	BC160-6*	6	P-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
29#	BC160-10*	6	P-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
30#	BC160-16*	6	P-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
31#	BC161-6*	6	P-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
32#	BC161-10*	6	P-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
33#	BC161-16*	6	P-PEΔ	Si	TO39	AØ	Pt 3.7W at 45°C case;Vsat 1.0V max;hFE 1/2 1.25 max
34	BC328/BC338	6	P-PE	Si	TO92	F	hFE1/2 1.25 typ, 1.4 max;Pt 500mW;BVCES 30V;ft 100MHz.
35	BC337/BC327	6	N-PE	Si	TO92	F	hFE1/2 1.25 typ, 1.4 max;Pt 500mW;BVCES 50V;ft 100MHz.
36#	BCY55*	6	N-PLØ	Si	F37	PL	Pt 300mW;IC1/2 .85 min;VBE(1-2) 4.0mV max;ΔV/ΔT 3.0uV/°C;ΔI/ΔT 1.5nA/°C.
37#	BCY87	6	N-PLØ	Si	TO71	PS	VBE(1-2)-3.0mV max;IB(1-2)-25nA max;ΔV/ΔT-1.0uV/deg.C.
38#	BCY88	6	N-PLØ	Si	TO71	PS	VBE(1-2)-6.0mV max;IB(1-2)-80nA max;ΔV/ΔT-2.0uV/deg.C.
39#	BCY89	6	N-PLØ	Si	TO71	PS	VBE(1-2)-10mV max;IB(1-2)-300nA max;ΔV/ΔT-4.0uV/deg.C.
40	BD181*	6	N-D	Si	TO3	CØ	BVCBO 55V;Pt 78W;hFE1/hFE2 1.3 max at Ic 3.0A,VCE 4.0V.
41	BD182*	6	N-D	Si	TO3	CØ	BVCBO 70V;Pt 117W;hFE1/hFE2 1.3 max at Ic 4.0A,VCE 4.0V.
42	BD183*	6	N-D	Si	TO3	CØ	BVCBO 85V;Pt 117W;hFE1/hFE2 1.3 max at Ic 3.0A,VCE 4.0V.
43#	BFQ10*	6	N	Si	TO71	PJ	dΔVGS/dT 5uV/°C;IΔVGS 5mV;ΔgoS/gfs 10uV/V;ID1-S1S/ID2-S2S 1.03max.
44#	BFQ11*	6	N	Si	TO71	PJ	dΔVGS/dT 5uV/°C;IΔVGS 10mV;ΔgoS/gfs 30uV/V;ID1-S1S/ID2-S2S 1.03max.
45#	BFQ12*	6	N	Si	TO71	PJ	dΔVGS/dT 10uV/°C;IΔVGS 10mV;ΔgoS/gfs 30uV/V;ID1-S1S/ID2-S2S 1.05max.
46#	BFQ13*	6	N	Si	TO71	PJ	dΔVGS/dT 20uV/°C;IΔVGS 10mV;ΔgoS/gfs 30uV/V;ID1-S1S/ID2-S2S 1.05max.
47#	BFQ14*	6	N	Si	TO71	PJ	dΔVGS/dT 20uV/°C;IΔVGS 15mV;ΔgoS/gfs 30uV/V;ID1-S1S/ID2-S2S 1.08max.
48#	BFQ15*	6	N	Si	TO71	PJ	dΔVGS/dT 40uV/°C;IΔVGS 20mV;ΔgoS/gfs 30uV/V;ID1-S1S/ID2-S2S 1.10max.
49#	BFQ16*	6	N	Si	TO71	PJ	dΔVGS/dT 50uV/°C;IΔVGS 50mV;ΔgoS/gfs 100uV/V;ID1-S1S/ID2-S2S 1.20max.
50#	BFW39	6	N	Si	R131		Pt-.40Wea;IC-30mA;hFE1/2-.90 min;VBE(1-2)-5mV;hFE-60 min.
51#	BFW39A	6	N	Si	R131		hFE1/2-.85 min;VBE(1-2)-2.0mV max;Pt-.50W.
52#	BFW40	6	N	Si	R131		Pt-.40Wea;IC-30mA;hFE1/2-.99 min;VBE(1-2)-5mV;hFE-150 min.
53#	BFW40A	6	N	Si	R131		Pt-.50W device;hFE1/2-1.1 max;ΔVBE-10uV/C deg max.
54#	BFX11*	6	P-DPE	Si	TO78		Pt-.40W each;ICBO-10nA max;hFE1/2-.80 min;ΔVBE-5.0mV max.
55#	BFX15*	6	N-PL	Si	TO78		Pt-.50W each;VBE1/2-5.0mV max;hFE1/2-.90 min;ICBO-10nA max.
56#	BFX36*	6	P-DPE	Si	TO77		Pt-.40W each;hFE1/hFE2-.90 min;VBE1/2-3.0mV max;ICBO-10nA max.
57#	BFX70*	6	N-DPLØ	Si	TO77		Pt-.6W;hFE1-2-.90 min;VBE(1-2)-5.0mV max;ΔVBE(1-2)/ΔT-10uV/deg.C.
58#	BFX71*	6	N-DPL	Si	TO77		Pt-.6W;hFE1-2-.80 min;VBE(1-2)-15mV max;ΔVBE(1-2)/ΔT-25uV/deg.C.
59#	BFX72*	6	N-DPL	Si	TO77		Pt-.6W;hFE1-2-.90 min;VBE(1-2)-5.0mV max;ΔVBE(1-2)/ΔT-25uV/deg.C.
60#	BFX99*	6	N-DPLØ	Si	TO77		Pt-.6W;hFE1-2-.90 min;VBE(1-2)-1.5mV max;ΔVBE(1-2)-.50mV max.
61#	BFY20	6	N-PL	Si	R131		ft-245Mc;BVCBO-40V;hFE-10 min./.10mA;10mV-VBE match;pt-.60W.
62#	BFY81	6	NDPL	Si	TO77		Pt-.60W;BVCBO-45V;ft-60Mc min;hFE1/2-.80 min;VBE(1-2)-10mV max.
63#	BFY82	6	NDPL	Si	TO77		Pt-.50W;BVCBO-60V;ft-250Mc min;hFE1/2-.80 min;VBE(1-2)-15mV max.
64#	BFY83	6	NDPL	Si	TO77		Pt-.60W;BVCBO-100V;ft-50Mc min;hFE1/2-.80 min;VBE(1-2)-15mV max.
65#	BFY84	6	NDPE	Si	TO77		Pt-.38W;BVCBO-30V;ft-600Mc min;hFE1/2-.80 min;VBE(1-2)-15mV max.
66#	BFY85*	6	N-PE	Si	R131c		Pt-260mW;hFE Diff. 20% max;VBE Diff. 10mV max.
67#	BFY86*	6	N-PE	Si	R131c		Pt-260mW;hFE Diff. 10% max;VBE Diff. 5.0mV max.
68#	BFY91	6	N-PL	Si	R131c		ft-60Mc;BVCEO-45V;hFE-60-240/10uA;5mV-VBE match;10%hFE match.
69#	BFY92	6	N-PL	Si	R131c		ft-60Mc;BVCEO-45V;hFE-60-240/10uA;10mV-VBE match;20%hFE match.
70#	C94EG	6	NØØ	Si	TO92	DA	IGSS 50uA max;GmIDSS VGS match 10%;VGS diff 10mV max;Drift 100uV/°C max.
71#	C94ER	6	NØØ	Si	TO92	DA	IGSS 50uA max;GmIDSS VGS match 5.0%;VGS diff 5.0mV max;Drift 50uV/°C max.
72#	C95EG	6	NØØ	Si	TO92	DA	IGSS 50uA max;GmIDSS VGS match 10%;VGS diff 10mV max;Drift 100uV/°C max.
73#	C95ER	6	NØØ	Si	TO92	DA	IGSS 50uA max;GmIDSS VGS match 5.0%;VGS diff 5.0mV max;Drift 50uV/°C max.
74#	C96EG	6	NØØ	Si	TO92	DA	IGSS 500uA max;GmIDSS VGS match 10%;VGS diff 20mV max;Drift 100uV/°C max.
75#	C97EG	6	N#	Si	TO92	DA	IGSS 50pA max;VGS diff 10mV;gfs IDSS VGS match 10%;Drift 100uV/°C max.
76#	C97ER	6	N#	Si	TO92	DA	IGSS 50pA max;VGS diff 5.0mV;gfs IDSS VGS match 5.0%;Drift 50uV/°C max.
77#	C98EG	6	N#	Si	TO92	DA	IGSS 50pA max;VGS diff 10mV;gfs IDSS VGS match 10%;Drift 100uV/°C max.
78#	C98ER	6	N#	Si	TO92	DA	IGSS 50pA max;VGS diff 5.0mV;gfs IDSS VGS match 5.0%;Drift 50uV/°C max.
79	DI5117/5120	6	P	Si			Chips;Match Char at Ic 10uA,Vce 5V-Vbe Diff 3.0mV Max,DC Gain Ratio 0.9-1.0
80	DI5118/5121	6	P	Si			Chips;Match Char at Ic 10uA,Vce 5V-Vbe Diff 5.0mV Max,DC Gain Ratio 0.85-1.0
81	DI5119-1	6	P	Si			Chips;Match Char at Ic 10uA,Vce 5V-Vbe Diff 10.0mV Max,DC Gain Ratio 0.8-1.0
82	DI5119/5122	6	P	Si			Chips;Match Char at Ic 10uA,Vce 5V-Vbe Diff 5.0mV Max,DC Gain Ratio 0.8-1.0
83#	ESM25*	6	N	Si	TO71	PJ	Pt 400mW(both sides);IDSS1/2 0.8min,1.0max;VGS(1-2)25mV max;VGS(1-2)/TΔ80uV/°C max.
84#	FT5320	6	N-PE	Si	R131d	PD	Pt 200mW(Each);BVCBO 150V;BVCEO 150V;hfe 1/2 .9 min, 1.0 max
85#	FT5321	6	P-PE	Si	R131d	PD	Pt 200mW(Each);BVCBO 150V;BVCEO 150V;hFE 1/2 .9 min,1.0 max
86	HA7807	6	P-A	Si	TO5		Pair of HA7806;Vo-2.0mV max.
87	HA7809	6	P-A	Si	TO5		Pair of HA7808; Vo-1.5mV max.
88	IMF5564*	6	N	Si	TO71	PC	Matched Dual JFETs:VGS(1-2)5.0mV;G-S Diff.Drift 10uV/°C,IDSS(1-2)1.0 Max
89	IMF5565*	6	N	Si	TO71	PC	Matched Dual JFETs:VGS(1-2)10mV;G-S Diff Drift 25uV/°C,IDSS(1-2)1.0 Max
90	IMF5566*	6	N	Si	TO71	PC	Matched Dual JFETs:VGS(1-2)20mV;G-S Diff Drift 50uV/°C,IDSS(1-2)1.0 Max
91	IMF5911	6	N*	Si	TO99	PFØ	DiElectrically Isolated;gfs1/gfs2 1.0max,0.95min;VGS(1-2)25mV;JFET
92	IMF5912	6	N*	Si	TO99	PFØ	DiElectrically Isolated;gfs1/gfs2 1.0max,0.95min;VGS(1-2)50mV;JFET
93	IMF6485*	6	N*		TO71	PJ	FET;Pt 500mW(both sides);VGS (1-2) 25mVmax;ΔVGS(1-2)/ΔT 40uV/°C
94	IT120*	6	N-PL	Si	TO78	PA	Pd 750mW(both sides)max;VBE(1-2)2.0mV max;IB(1-2)5.0nA max.
95	IT120A*	6	N-PL	Si	TO78	PA	Pd 750mW(both sides)max;VBE(1-2)1.0mV max;IB(1-2)2.5nA max.
96	IT121*	6	N-PL	Si	TO78	PA	Pd 750mW(both sides)max;VBE(1-2)3.0mV max;IB(1-2)25nA max.
97	IT122*	6	N-PL	Si	TO78	PA	Pd 750mW(both sides)max;VBE(1-2)5.0mV max;IB(1-2)25nA max.
98	IT124*	6	N-PLØ	Si	TO78	PA	Pd 750mW(both sides);VBE(1-2) 2.0mV;VBE(1-2)/°C 5.0uV/°C;IB(1-2) 600pA max.
99	IT125	6	N-PL	Si	TO78	PA	Pd 750mW(Both Sides);VBE(1-2)2.0mVtyp;IB(1-2)600pAmax;Cc1c2 800fFmax;Ic1c2 250pAmax
100	IT126*	6	N-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)1.0mV max;IB(1-2)2.5nA max.
101	IT127*	6	N-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)2.0mV max;IB(1-2)5.0nA max.
102	IT128*	6	N-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)3.0mV max;IB(1-2)10nA max.
103	IT129*	6	N-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)5.0mV max;IB(1-2)20nA max.
104	IT130*	6	P-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)2.0mV max;IB(1-2)5.0nA max.
105	IT130A*	6	P-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)1.0mV max;IB(1-2)2.5nA max.
106	IT131*	6	P-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)3.0mV max;IB(1-2)25nA max.
107	IT132*	6	P-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)5.0mV max;IB(1-2)25nA max.
108	IT136*	6	P-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)1.0mV max;IB(1-2)2.5nA max.
109	IT137	6	P-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)2.0mV max;IB(1-2)5.0nA max.
110	IT138	6	P-PL	Si	TO78	PA	Pt 750mW(both sides)max;VBE(1-2)3.0mV max;IB(1-2)10nA max.